

# PNP SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

## FXT790A

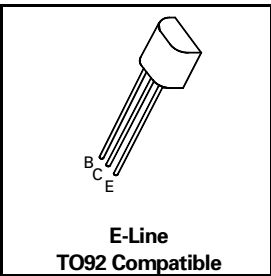
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**FEATURES**

- \* 40 Volt  $V_{CE0}$
- \* Gain of 200 at  $I_C=1$  Amps
- \* Very low saturation voltage

**APPLICATIONS**

- \* Darlington replacement
- \* Siren driver
- \* Battery powered circuits
- \* Motor drivers



**ABSOLUTE MAXIMUM RATINGS.**

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-40	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-6	A
Continuous Collector Current	$I_C$	-2	A
Practical Power Dissipation*	$P_{totp}$	1.5	W
Power Dissipation at $T_{amb}=25^{\circ}C$ derate above $25^{\circ}C$	$P_{tot}$	1 5.7	W mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^{\circ}C$

\*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

**ELECTRICAL CHARACTERISTICS (at  $T_{amb} = 25^{\circ}C$ )**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-50			V	$I_C=-100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40			V	$I_C=-10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E=-100\mu A$
Collector Cut-Off Current	$I_{CBO}$			-0.1	$\mu A$	$V_{CB}=-30V$
Emitter Cut-Off Current	$I_{EBO}$			-0.1	$\mu A$	$V_{EB}=-4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.25 -0.45 -0.75	V	$I_C=500mA, I_B=5mA^*$ $I_C=1A, I_B=10mA^*$ $I_C=2A, I_B=50mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.0	V	$I_C=1A, I_B=10mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.75		V	$I_C=-1A, V_{CE}=-2V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	300 250 200 150		800		$I_C=10mA, V_{CE}=-2V^*$ $I_C=500mA, V_{CE}=-2V^*$ $I_C=1A, V_{CE}=-2V^*$ $I_C=2A, V_{CE}=-2V^*$

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## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	$f_T$	100			MHz	$I_C = -50\text{mA}$ , $V_{CE} = -5\text{V}$ $f = 50\text{MHz}$
Input Capacitance	$C_{ibo}$		225		pF	$V_{EB} = -0.5\text{V}$ , $f = 1\text{MHz}$
Output Capacitance	$C_{obo}$		24		pF	$V_{CB} = -10\text{V}$ , $f = 1\text{MHz}$
Switching Times	$t_{on}$ $t_{off}$		35 600		ns ns	$I_C = -500\text{mA}$ , $I_{B1} = -50\text{mA}$ $I_{B2} = -50\text{mA}$ , $V_{CC} = -10\text{V}$

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

## THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient <sub>1</sub>	$R_{th(j-amb)1}$	175	$^{\circ}\text{C/W}$
Junction to Ambient <sub>2</sub>	$R_{th(j-amb)2} \dagger$	116	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-case)}$	70	$^{\circ}\text{C/W}$

† Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.

